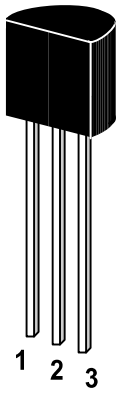
ST 2SC3203

NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into tow group, O and Y and according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25?)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	35	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Emitter Current	I_E	-800	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	^{O}C
Storage Temperature Range	T_S	-55 to +150	^{O}C

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Characteristics at T_{amb}=25 ^{o}C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at V_{CE}=1V, I_C=100mA					
Current Gain Group O	h_{FE}	100	-	200	-
Y	h_{FE}	160	-	320	-
at V_{CE}=1V, I_C=700mA	h_{FE}	35	-	-	-
Collector Cutoff Current					
at V_{CB}=35V	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current					
at V_{EB}=5V	I_{EBO}	-	-	0.1	μA
Collector Emitter Saturation Voltage					
at I_C=500mA, I_B=20mA	$V_{CE(sat)}$	-	-	0.5	V
Transition Frequency					
at V_{CE}=5V, I_C=10mA	f_T	-	120	-	MHz
Base Emitter Voltage					
at I_C=10mA, V_{CE}=1V	V_{BE}	0.5	-	0.8	V
Collector Output Capacitance					
at V_{CB}=10V, f=1MHz	C_{OB}	-	13	-	pF
Collector Emitter Breakdown Voltage					
at I_C=10mA	V_{CEO}	30	-	-	V

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